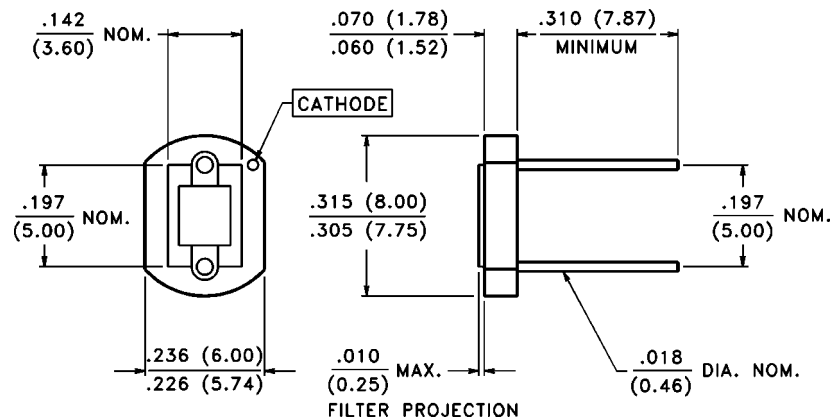


## PACKAGE DIMENSIONS inch (mm)



CASE 21F 8 mm CERAMIC  
CHIP ACTIVE AREA: .008 in<sup>2</sup> (5.16 mm<sup>2</sup>)

## PRODUCT DESCRIPTION

Planar silicon photodiode in recessed ceramic package. The package incorporates an infrared rejection filter. These diodes have very high shunt resistance and have good blue response.

## ABSOLUTE MAXIMUM RATINGS

Storage Temperature:

-20°C to 75°C

Operating Temperature:

-20°C to 75°C

**RoHS Compliant**



## ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also VTB curves, pages 21-22)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VTB8440BH			VTB8441BH			UNITS
			Min.	Typ.	Max.	Min.	Typ.	Max.	
I <sub>SC</sub>	Short Circuit Current	H = 100 fc, 2850 K	4	5		4	5		μA
TC I <sub>SC</sub>	I <sub>SC</sub> Temperature Coefficient	2850 K		.02	.08		.02	.08	%/°C
V <sub>OC</sub>	Open Circuit Voltage	H = 100 fc, 2850 K		420			420		mV
TC V <sub>OC</sub>	V <sub>OC</sub> Temperature Coefficient	2850 K		-2.0			-2.0		mV/°C
I <sub>D</sub>	Dark Current	H = 0, V <sub>R</sub> = 2.0 V			2000			100	pA
R <sub>SH</sub>	Shunt Resistance	H = 0, V = 10 mV		.07			1.4		GΩ
TC R <sub>SH</sub>	R <sub>SH</sub> Temperature Coefficient	H = 0, V = 10 mV		-8.0			-8.0		%/°C
C <sub>J</sub>	Junction Capacitance	H = 0, V = 0		1.0			1.0		nF
λ <sub>range</sub>	Spectral Application Range		330		720	330		720	nm
λ <sub>p</sub>	Spectral Response - Peak			580			580		nm
V <sub>BR</sub>	Breakdown Voltage		2	40		2	40		V
θ <sub>1/2</sub>	Angular Resp. - 50% Resp. Pt.			±50			±50		Degrees
NEP	Noise Equivalent Power		1.1 x 10 <sup>-13</sup> (Typ.)			2.4 x 10 <sup>-14</sup> (Typ.)			W/√Hz
D*	Specific Detectivity		2.2 x 10 <sup>12</sup> (Typ.)			9.7 x 10 <sup>12</sup> (Typ.)			cm√Hz/W